

SWITCHING REGULATOR APPLICATIONS

Features

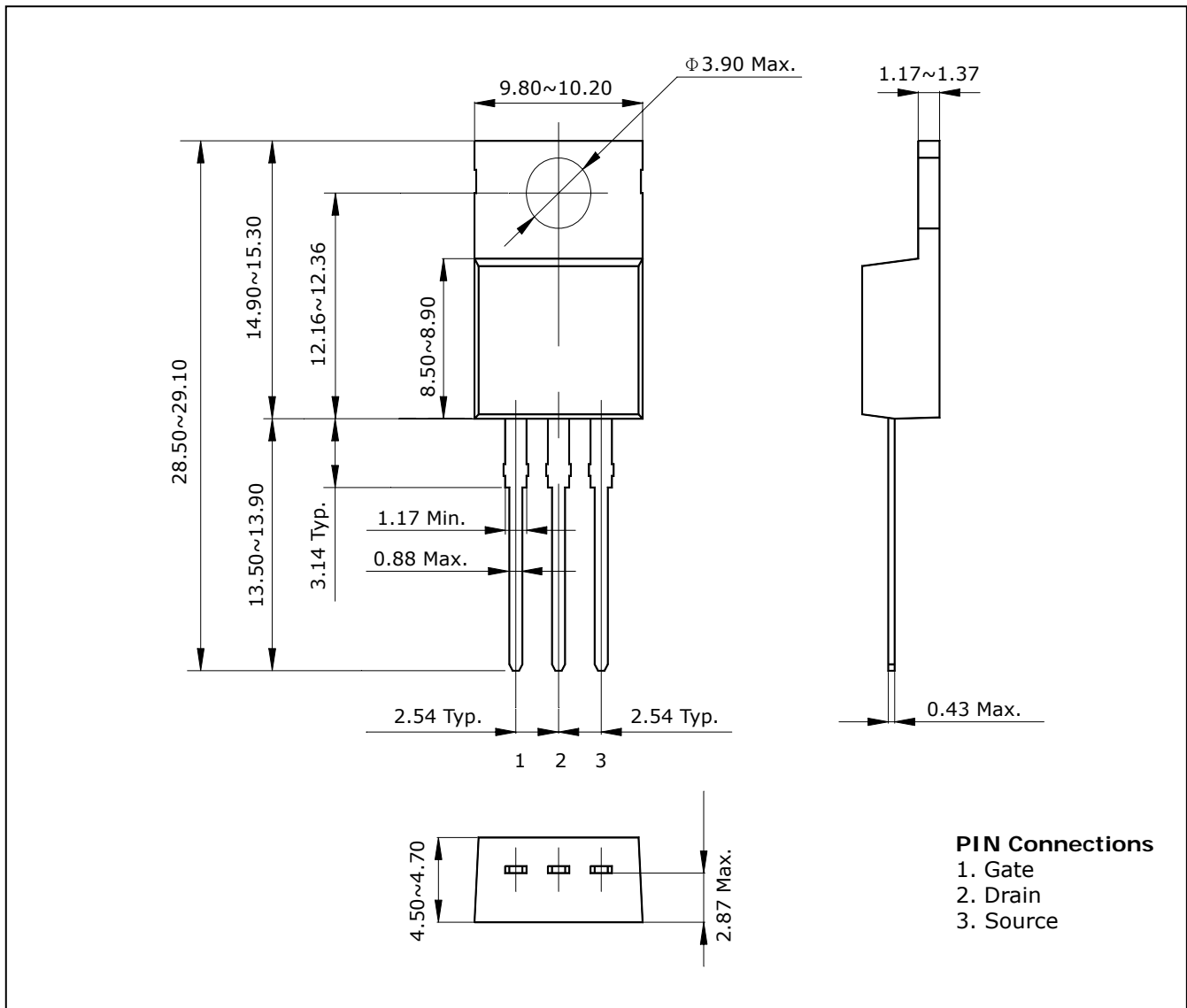
- High Voltage: $BV_{DSS}=500V(\text{Min.})$
- Low C_{rSS} : $C_{rSS}=8.4pF(\text{Typ.})$
- Low gate charge : $Qg=17nC(\text{Typ.})$
- Low $R_{DS(on)}$: $R_{DS(on)}=1.5\Omega(\text{Max.})$

Ordering Information

| Type NO. | Marking | Package Code |
|----------|---------|--------------|
| STK830P | STK830 | TO-220AB-3L |

Outline Dimensions

unit : mm



Absolute maximum ratings

(Tc=25°C)

| Characteristic | Symbol | Rating | Unit | |
|----------------------------------|-----------|-------------------------|------|---|
| Drain-source voltage | V_{DSS} | 500 | V | |
| Gate-source voltage | V_{GSS} | ±30 | V | |
| Drain current (DC) | I_D | $T_C=25^\circ\text{C}$ | 4.5 | A |
| | | $T_C=100^\circ\text{C}$ | 2.7 | A |
| Drain current (Pulsed) * | I_{DM} | 18 | A | |
| Drain power dissipation | P_D | 71 | W | |
| Avalanche current (Single) ② | I_{AS} | 4.5 | A | |
| Single pulsed avalanche energy ② | E_{AS} | 250 | mJ | |
| Avalanche current (Repetitive) ① | I_{AR} | 4.5 | A | |
| Repetitive avalanche energy ① | E_{AR} | 5.0 | mJ | |
| Junction temperature | T_J | 150 | °C | |
| Storage temperature range | T_{stg} | -55~150 | °C | |

* Limited by maximum junction temperature

| Characteristic | | Symbol | Typ. | Max | Unit |
|--------------------|------------------|---------------|------|------|------|
| Thermal resistance | Junction-case | $R_{th(J-C)}$ | - | 1.75 | °C/W |
| | Junction-ambient | $R_{th(J-A)}$ | - | 62.5 | |

Electrical Characteristics

(Tc=25°C)

| Characteristic | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|--------------------------------|---------------|---|------|------|-----------|----------|
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $I_D=250\ \mu A, V_{GS}=0V$ | 500 | - | - | V |
| Gate threshold voltage | $V_{GS(th)}$ | $I_D=250\ \mu A, V_{DS}=V_{GS}$ | 2.0 | - | 4.0 | V |
| Drain-source cut-off current | I_{DSS} | $V_{DS}=500V, V_{GS}=0V$ | - | - | 10 | μA |
| Gate leakage current | I_{GSS} | $V_{DS}=0V, V_{GS}=\pm 30V$ | - | - | ± 100 | nA |
| Drain-source on-resistance ④ | $R_{DS(on)}$ | $V_{GS}=10V, I_D=2.25A$ | - | - | 1.5 | Ω |
| Forward transfer conductance ④ | g_{fs} | $V_{DS}=10V, I_D=2.25A$ | - | 3.3 | - | S |
| Input capacitance | C_{iss} | $V_{GS}=0V, V_{DS}=25V$ $f=1\ MHz$ | - | 550 | 830 | pF |
| Output capacitance | C_{oss} | | - | 46 | 70 | |
| Reverse transfer capacitance | C_{rss} | | - | 8.4 | 15 | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}=250V, I_D=4.5A$ $R_G=12\ \Omega$ | - | 12 | - | ns |
| Rise time | t_r | | - | 46 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 50 | - | |
| Fall time | t_f | | - | 48 | - | |
| Total gate charge | Q_g | $V_{DS}=250V, V_{GS}=10V$ $I_D=4.5A$ | - | 17 | 26 | nC |
| Gate-source charge | Q_{gs} | | - | 2.6 | 4.0 | |
| Gate-drain charge | Q_{gd} | | - | 5.8 | 9.0 | |

Source-Drain Diode Ratings and Characteristics

(Tc=25°C)

| Characteristic | Symbol | Test Condition | Min | Typ | Max | Unit |
|---------------------------|----------|---|-----|-----|-----|---------|
| Source current (DC) | I_S | Integral reverse diode in the MOSFET | - | - | 4.5 | A |
| Source current (Pulsed) ① | I_{SP} | | - | - | 18 | |
| Forward voltage ④ | V_{SD} | $V_{GS}=0V, I_S=4.5A$ | - | - | 1.4 | V |
| Reverse recovery time | t_{rr} | $I_S=4.5A, V_{GS}=0V$ $dI_S/dt=100A/\mu s$ | - | 188 | - | ns |
| Reverse recovery charge | Q_{rr} | | - | 2.1 | - | μC |

Note ;

- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ② $L=20mH, I_{AS}=4.5A, V_{DD}=50V, R_G=27\ \Omega$
- ③ Pulse Test : Pulse width $\leq 400\ \mu s$, Duty cycle $\leq 2\%$
- ④ Essentially independent of operating temperature

Electrical Characteristic Curves

Fig. 1 $I_D - V_{DS}$

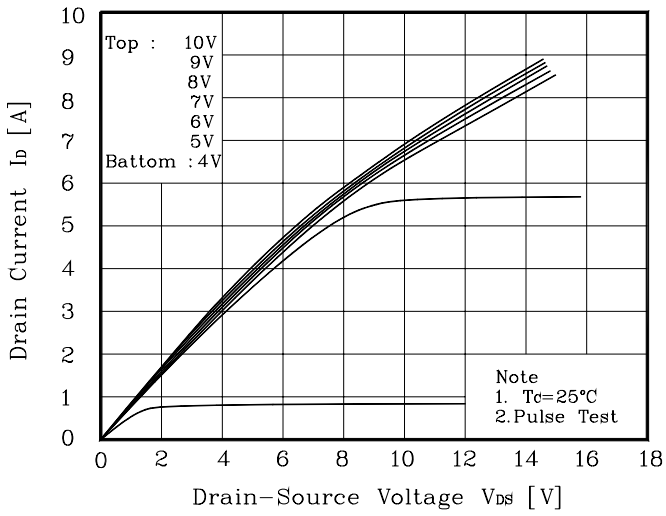


Fig. 2 $I_D - V_{GS}$

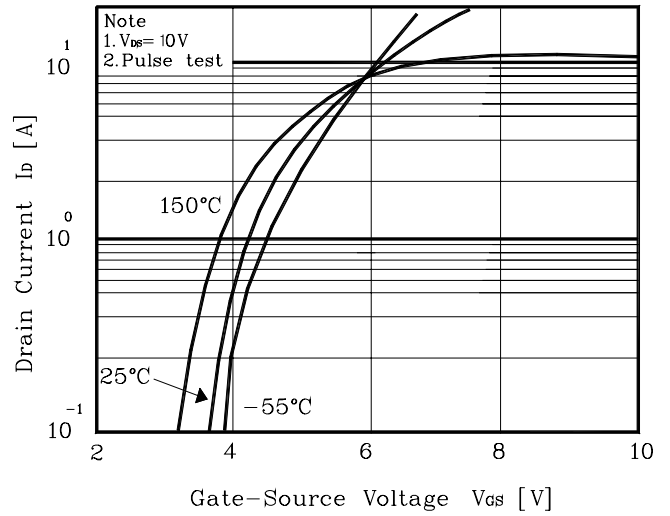


Fig. 3 $R_{DS(on)} - I_D$

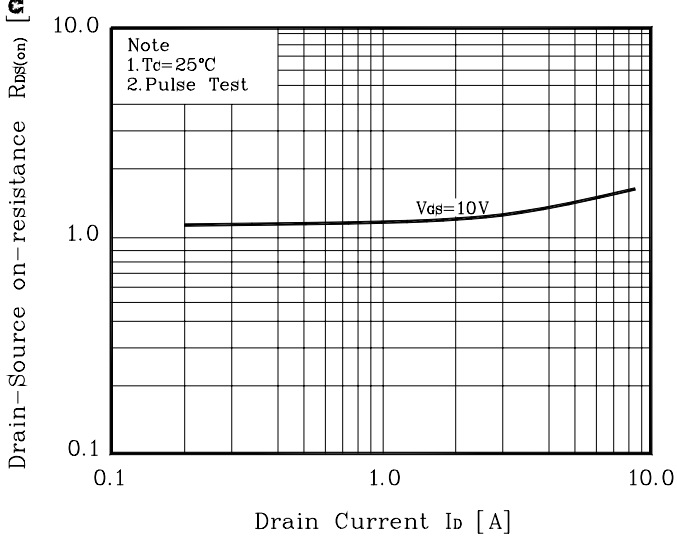


Fig. 4 $I_S - V_{SD}$

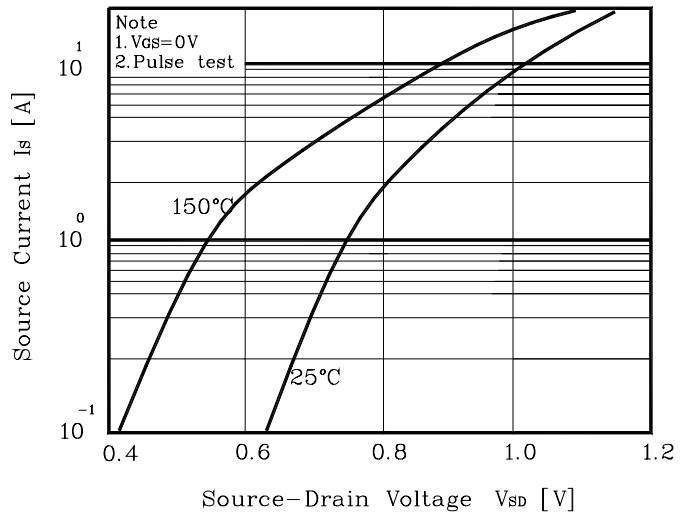


Fig. 5 Capacitance - V_{DS}

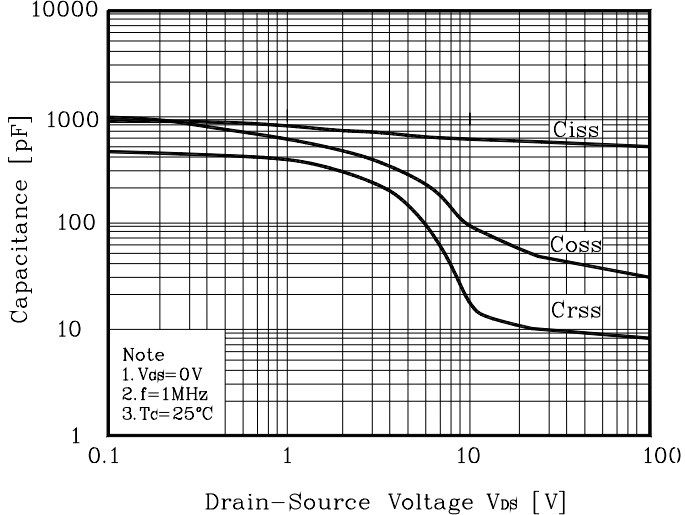


Fig. 6 $V_{GS} - Q_G$

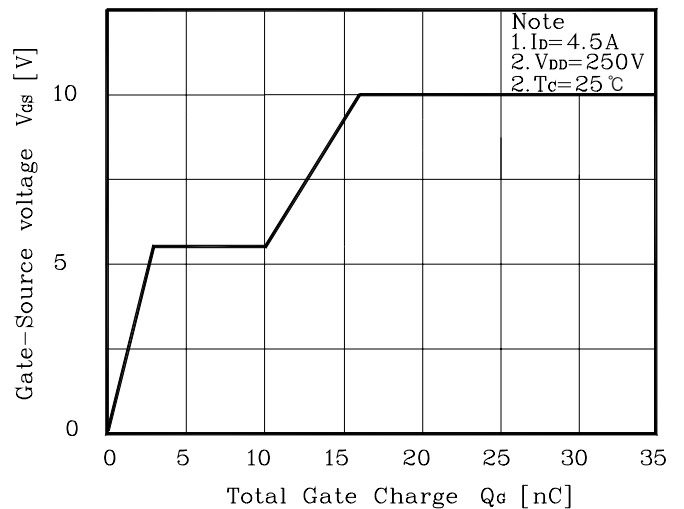


Fig. 7 $V_{(BR)DSS} - T_J$

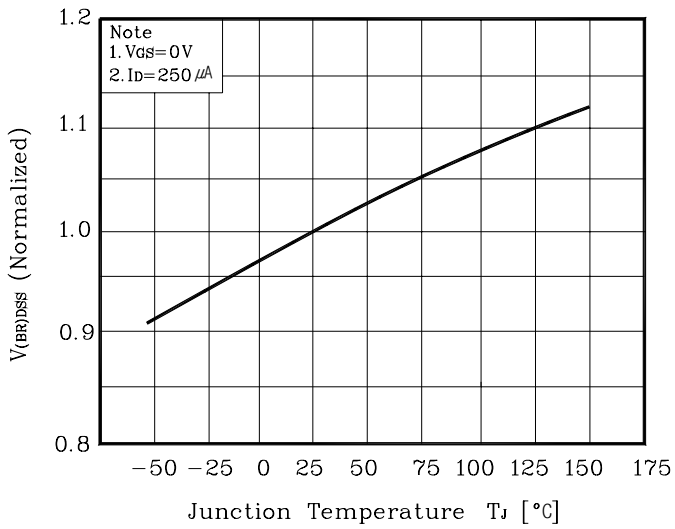


Fig. 8 $R_{DS(on)} - T_J$

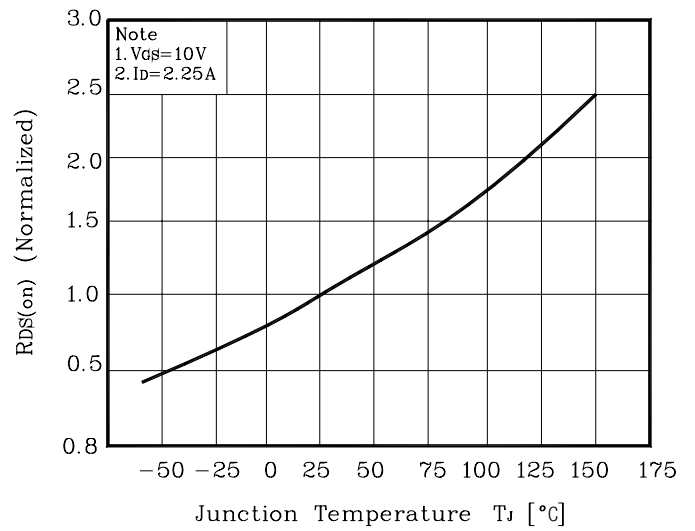


Fig. 9 $I_D - T_C$

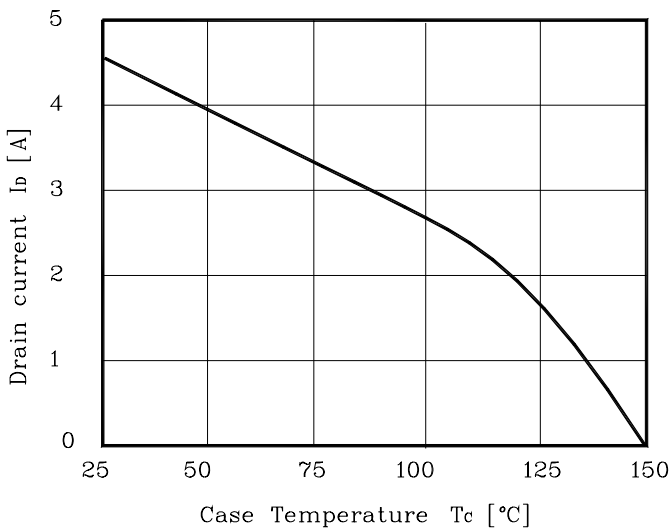


Fig. 10 Safe Operating Area

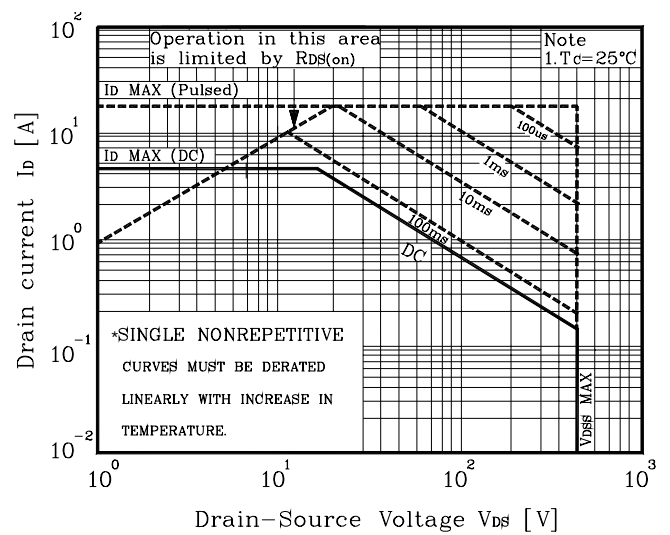


Fig. 11 Gate Charge Test Circuit & Waveform

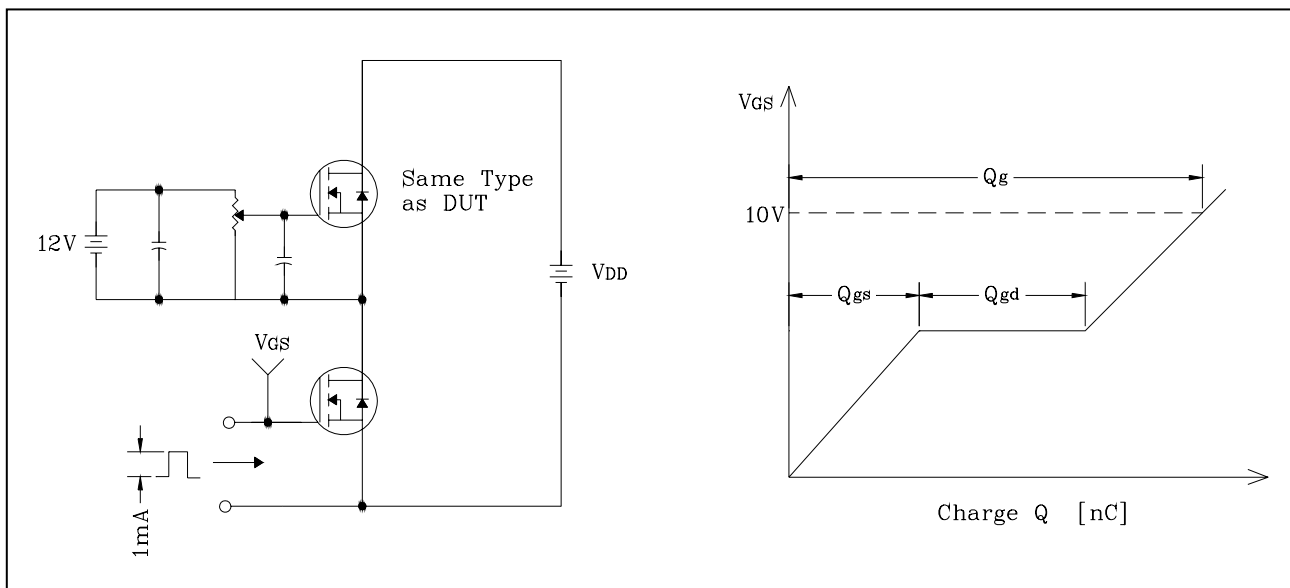


Fig. 12 Switching Time Test Circuit & Waveform

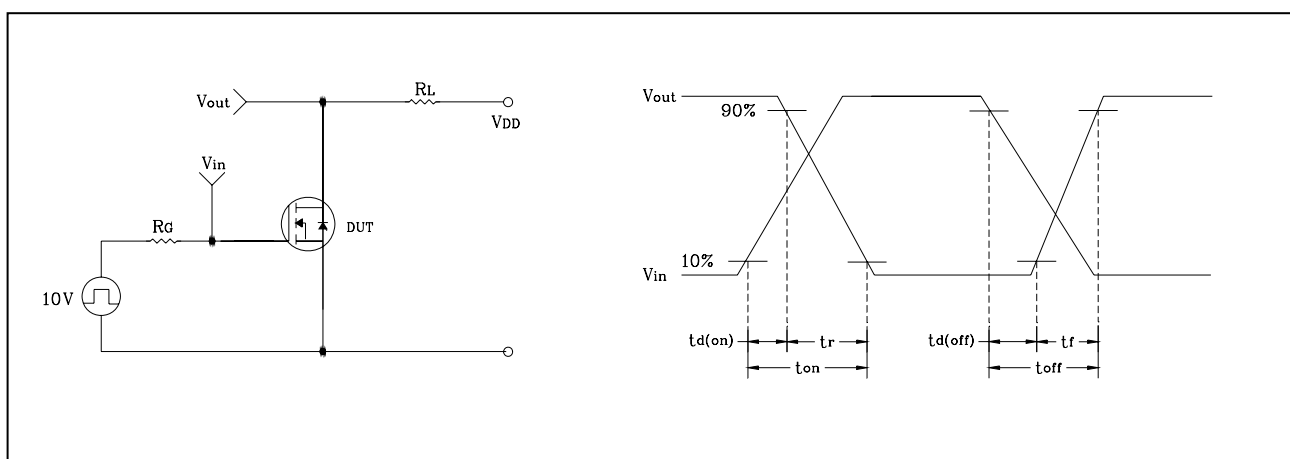


Fig. 13 E_{AS} Test Circuit & Waveform

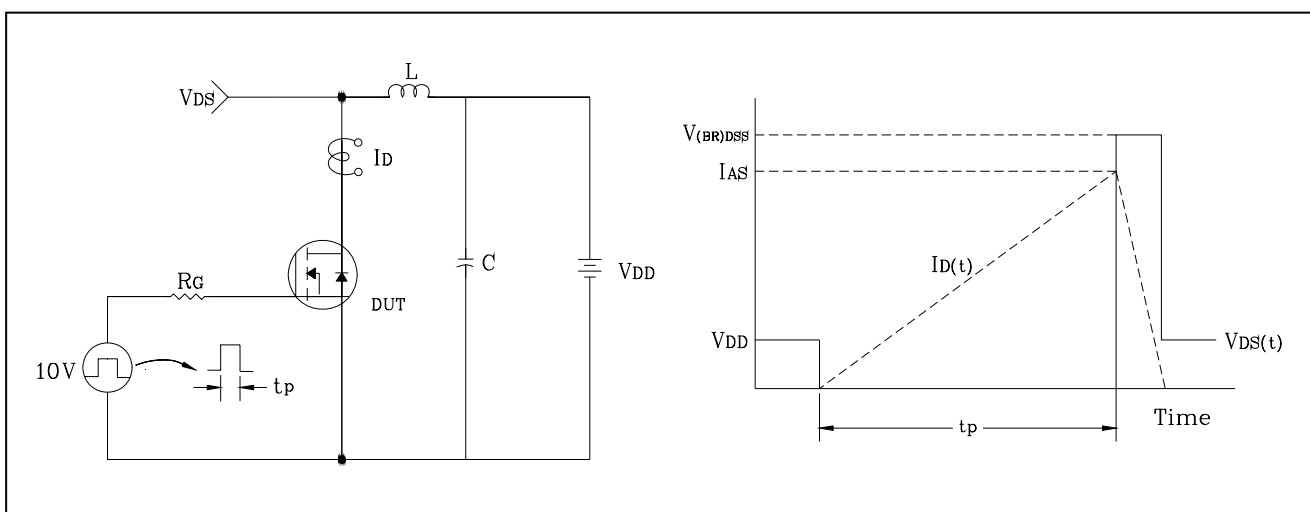
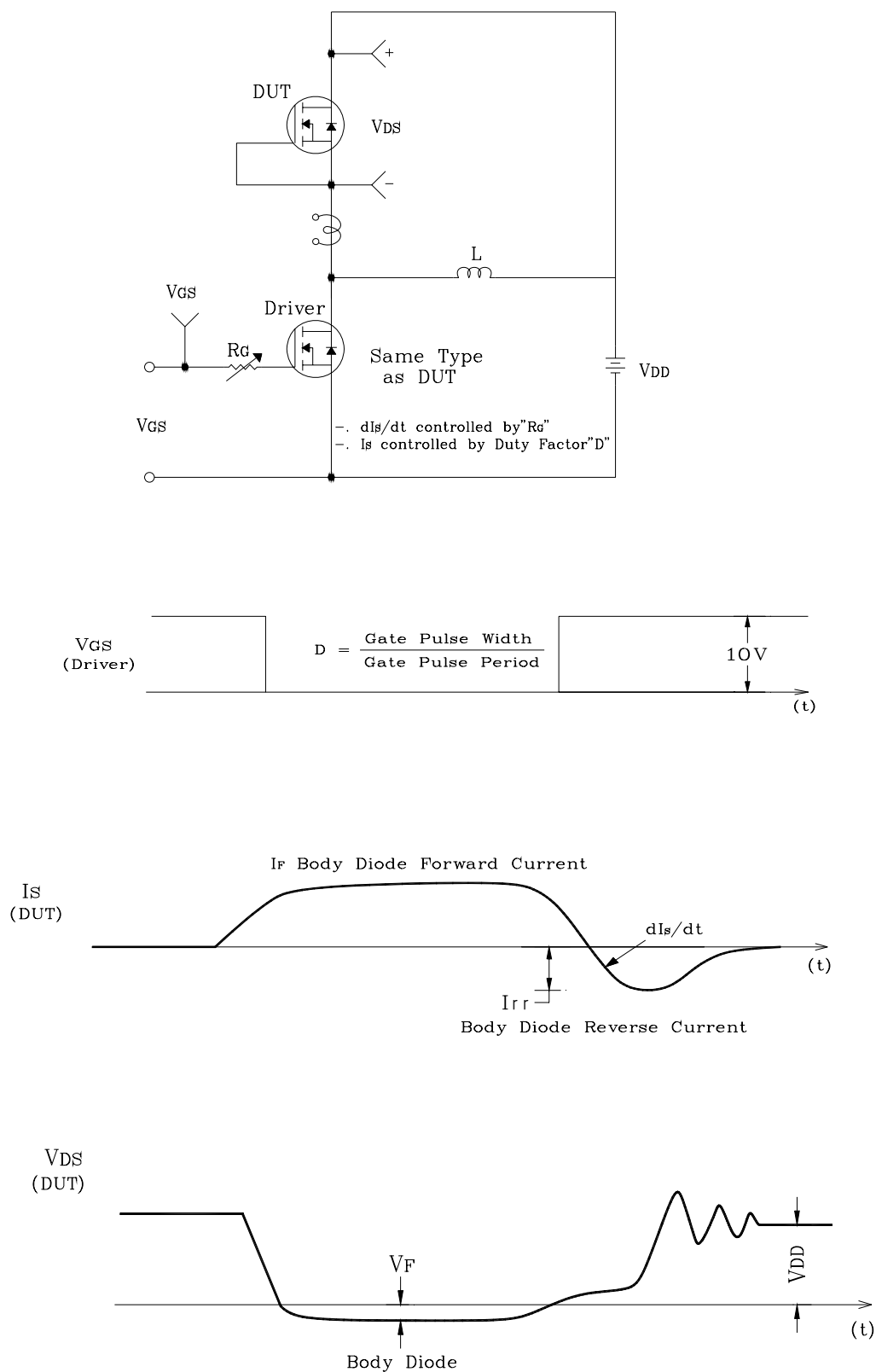


Fig. 14 Peak Diode Recovery dv/dt Test Circuit & Waveform



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